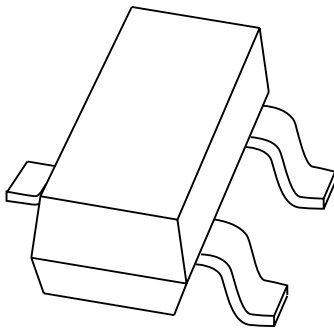


# DATA SHEET



**PBSS5120T**

20 V, 1 A

PNP low  $V_{CEsat}$  (BISS) transistor

# 20 V, 1 A PNP low $V_{CEsat}$ (BISS) transistor

**PBSS5120T**

### FEATURES

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative for MOSFETs in specific applications.

### APPLICATIONS

- Power management
  - DC/DC conversion
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load drivers (e.g. relays, buzzers and motors).

### DESCRIPTION

PNP BISS transistor in a SOT23 plastic package providing ultra low  $V_{CEsat}$  and  $R_{CEsat}$  parameters.  
NPN complement: PBSS4120T.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS5120T	*3K

### Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.  
\* = W: made in China.

### ORDERING INFORMATION

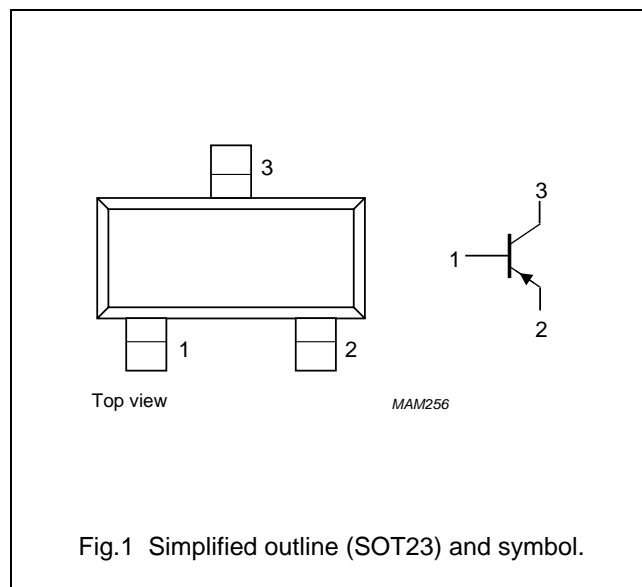
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5120T	–	plastic surface mounted package; 3 leads	SOT23

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	–20	V
$I_C$	collector current (DC)	–1	A
$I_{CM}$	peak collector current	–2	A
$R_{CEsat}$	equivalent on-resistance	250	m $\Omega$

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–20	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–1	A
$I_{CM}$	peak collector current		–	–2	A
$I_{BM}$	peak base current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 2	–	480	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Notes**

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

**Notes**

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

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**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -20\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -20\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	300	450	–	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$	250	350	–	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}$	200	290	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–	–100	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–125	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ note 1	–	–	250	$\text{m}\Omega$
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	–	–	–0.75	V
$f_T$	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	28	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

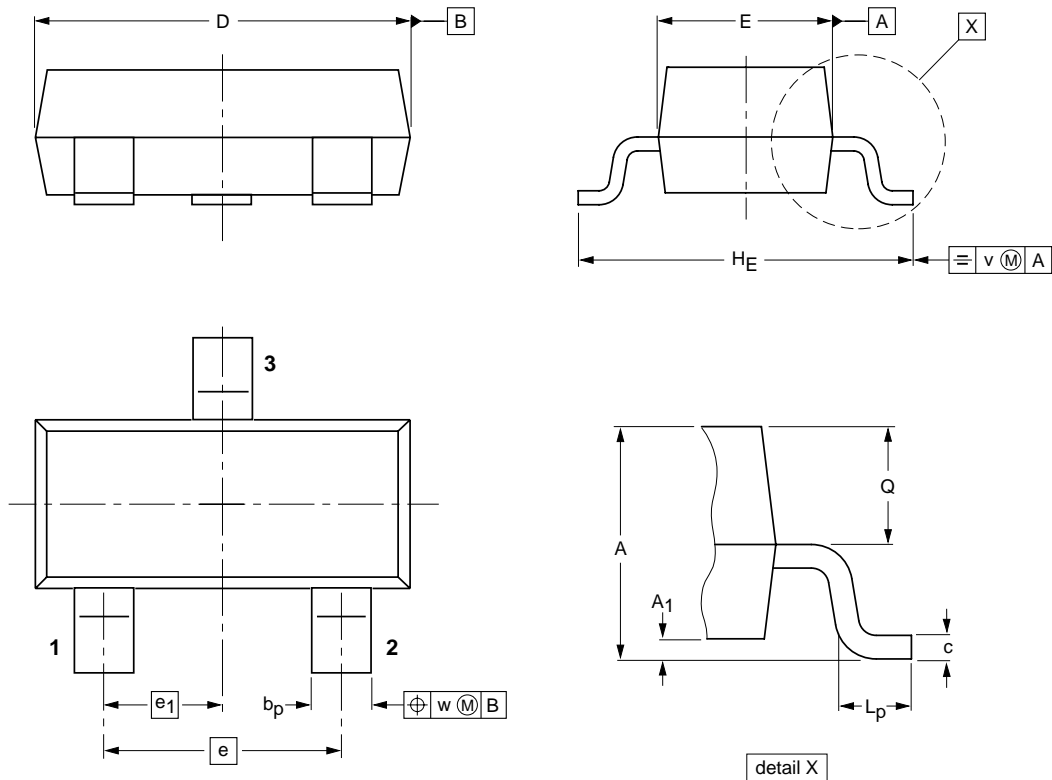
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13

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**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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